2. (Amended) A system for processing a semiconductor device, the system comprising:

a processing chamber; and

a first plate positioned within said processing chamber and defining a first internal cavity configured to receive a first gas through a first passage into said first internal cavity at a first temperature and to emit said first gas from said first internal cavity at a second temperature through a second passage; and

a second plate disposed adjacent to said first plate, wherein said second plate defines a second internal cavity configured to receive a second gas through a first passage into said second internal cavity at a first temperature and to emit said gas from said second internal cavity at a second temperature through a second passage.

3. (Amended) The system of Claim 2, wherein said second passage comprise a plurality of holes defined on a surface of said first and said second plates.

4. (Amended) The system of Claim 2, wherein said first plate and said second plate comprise a heat source for heating said plate to a preselected temperature.

5. (Amended) The system of Claim 2, wherein said first gas is taken from the group consisting of N_2, He, H_2, O_2, Ar and gas mixtures containing He, H_2, O_2, Ar and N_2.

6. (Amended) The system of Claim 2, wherein said internal cavity further comprises a buffer to disperse said first gas throughout said internal cavity.

7. (Amended) A system for wafer processing comprising:

a chamber; and

at least one heatable plate positionable within said chamber, including:

an internal cavity defining an internal wall and configured to receive a gas at a first temperature;

means for heating said internal wall to a preselected temperature; and

an outlet portion defining a plurality of holes for emitting said gas at a second temperature.

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8. (Amended) A system for wafer processing comprising:

a chamber; and

at least one heatable plate positionable within said chamber, including:

an internal cavity defining an internal wall and configured to receive a gas;

means for heating said internal wall to a preselected temperature; and

an outlet portion defining a plurality of holes for emitting said gas; said at least one heatable plate including a first heatable plate and a second heatable plate disposed having adjacent surfaces configured to receive a wafer therebetween.

9. (Amended) The system of Claim 8, wherein said gas is taken from the group consisting of He, H_2, O_2, Ar, N_2 and gas mixtures containing He, H_2, O_2, Ar, and N_2.

10. (Amended) The system of Claim 8, wherein said internal cavity further comprises a buffer to disperse said first gas throughout said internal cavity.

Please cancel Claims 11 and 12.

Please add new Claims 13-16.

--13. (New) The system of Claim 1, wherein said first gas is taken from the group consisting of N_2, He, H_2, O_2, Ar and gas mixtures containing He, H_2, O_2, Ar and N_2.

14. (New) The system of Claim 1, wherein said internal cavity further comprises a buffer to disperse said first gas throughout said internal cavity.

15. (New) The system of Claim 7, wherein said gas is taken from the group consisting of He, H_2, O_2, Ar, N_2 and gas mixtures containing He, H_2, O_2, Ar, and N_2.

16. (New) The system of Claim 7, wherein said internal cavity further comprises a buffer to disperse said first gas throughout said internal cavity.--

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